

ABSTRACT

A method of manufacturing a semiconductor device includes the steps of, (1) preparing an SOI substrate, (2) forming a metal layer on the SOI substrate, (3) performing a first anneal treatment to the metal layer at a relatively low temperature in order to transform the metal layer to a first silicide layer, (4) forming an insulating layer on the first silicide layer, and (5) forming a contact hole, which reaches the first silicide layer, in the insulating layer; and (6) performing a second anneal treatment to the silicide layer at a relatively high temperature in order to transform the first silicide layer to a second silicide layer.